

Silicon PNP Power Transistors 2N5597 2N5599 2N5601 2N5603

DESCRIPTION

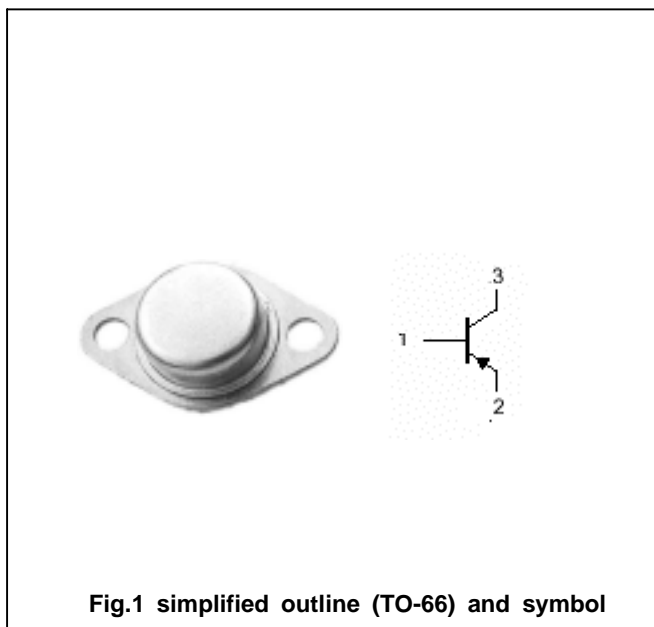
- With TO-66 package
- Excellent safe operating area
- Low collector-emitter saturation voltage

APPLICATIONS

- For high frequency power amplifier ; audio power amplifier and drivers.

PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |



Absolute maximum ratings(Ta=)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|--------------------|---------|------|
| V _{CBO} | Collector-base voltage | 2N5597 | 60 | V |
| | | 2N5599/5601 | 80 | |
| | | 2N5603 | 100 | |
| V _{CEO} | Collector-emitter voltage | 2N5597 | 80 | V |
| | | 2N5599/5601 | 100 | |
| | | 2N5603 | 120 | |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 2 | A |
| P _D | Total power dissipation | T _C =25 | 20 | W |
| T _j | Junction temperature | | 150 | |
| T _{stg} | Storage temperature | | -65~150 | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | VALUE | UNIT |
|---------------------|-------------------------------------|-------|------|
| R _{th-j-c} | Thermal resistance junction to case | 4.37 | /W |

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CHARACTERISTICST_j=25 unless otherwise specified

| SYMBOL | PARAMETER | | CONDITIONS | MIN | TYP. | MAX | UNIT |
|--------------------|--------------------------------------|-------------|--|-----|------|-----|------|
| V _{CEO} | Collector-emitter sustaining voltage | 2N5597 | I _C =50mA ; I _B =0 | 60 | | | V |
| | | 2N5599/5601 | | 80 | | | |
| | | 2N5603 | | 100 | | | |
| V _{CEsat} | Collector-emitter saturation voltage | | I _C =1A; I _B =0.1A | | | 1.0 | V |
| V _{BE} | Base-emitter on voltage | | I _C =1A ; V _{CE} =5V | | | 1.5 | V |
| I _{CB0} | Collector cut-off current | | V _{CB} =Rated V _{CB0} ; I _E =0 | | | 0.1 | mA |
| I _{CEO} | Collector cut-off current | | V _{CE} = Rated V _{CEO} ; I _B =0 | | | 1.0 | mA |
| I _{EBO} | Emitter cut-off current | | V _{EB} =5V; I _C =0 | | | 0.1 | mA |
| h _{FE} | DC current gain | 2N5597/5601 | I _C =1A ; V _{CE} =5V | 70 | | 200 | |
| | | 2N5599/5603 | | 30 | | 90 | |
| f _T | Transition frequency | 2N5597/5601 | I _C =0.5A ; V _{CE} =10V | 60 | | | MHz |
| | | 2N5599/5603 | | 50 | | | |

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PACKAGE OUTLINE

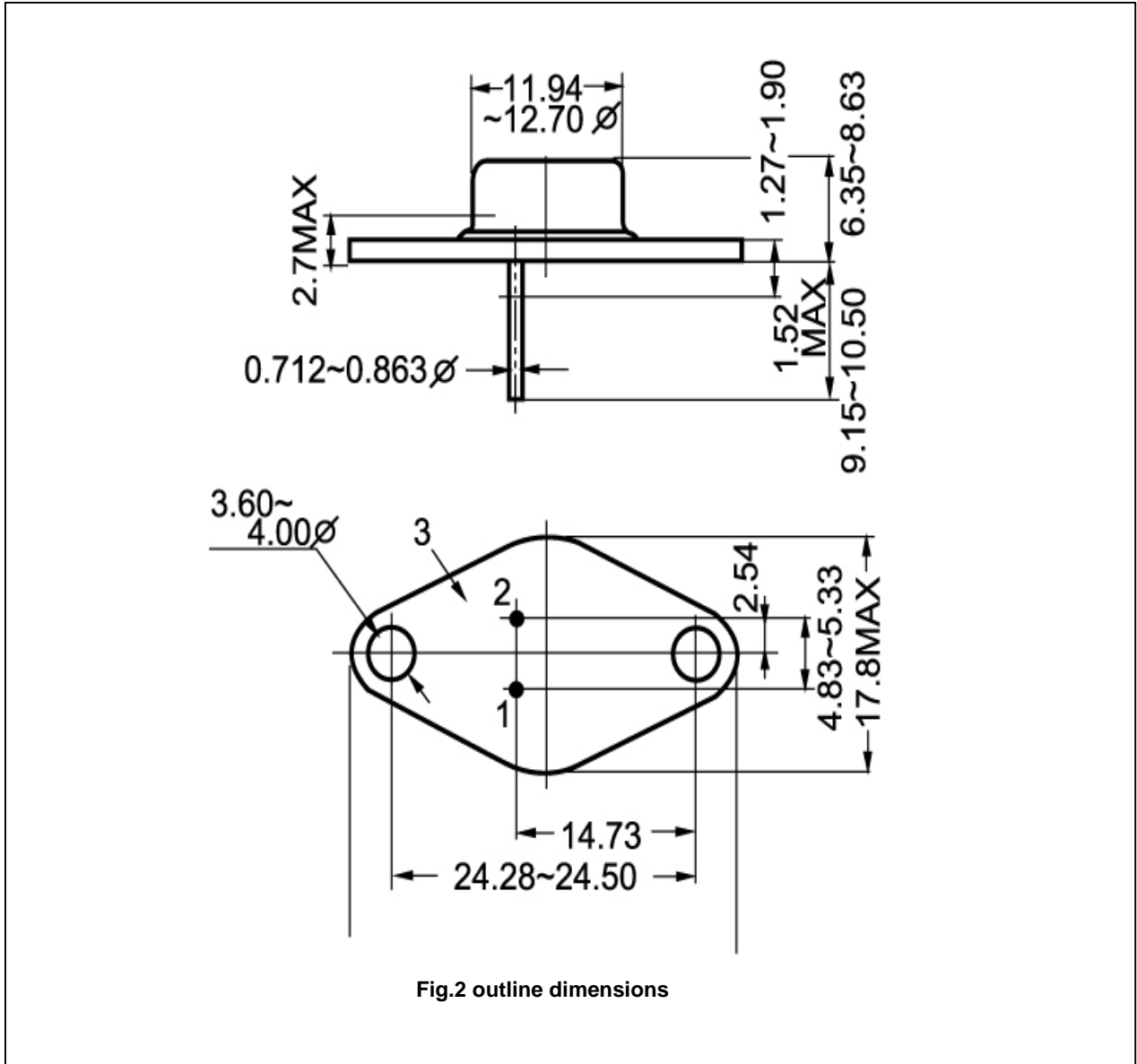


Fig.2 outline dimensions